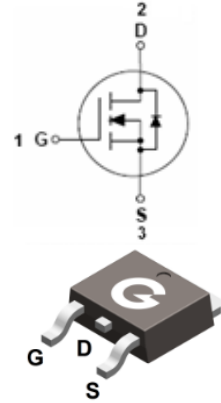


Features

- Fast switching
- Low on resistance
- Low gate charge
- Low reverse transfer capacitances
- HBM: JESD22-A114-B: 1B
- RoHS compliant with Halogen-free

HF



TO-252

Mechanical Data

- Case: TO-252
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL18N20HD	TO-252	80 pcs / Tube or 2500 pcs / Tape & Reel	18N20HD

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	200	V
Gate-to-Source Voltage	V _{GSS}	±30	V
Continuous Drain Current (T _C = 25°C)	I _D	18	A
Continuous Drain Current (T _C = 100°C)		11.3	A
Pulsed Drain Current	I _{DM}	72	A
Single Pulse Avalanche Energy ^{*4}	E _{AS}	500	mJ
Power Dissipation (T _C = 25°C)	P _D	100	W
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	0.9	1.25	°C/W
Thermal Resistance Junction-to-Air ^{*1}	R _{θJA}	-	30	50	°C/W
Thermal Resistance Junction-to-Air ^{*2}		-	-	100	°C/W

Electrical Characteristics (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	200	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *3	V _{GS} = 10V, I _D = 9A	-	0.16	0.18	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	2.7	4	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	2.8	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	1147	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 25V	-	141	-	
C _{RSS}	Reverse Transfer Capacitance	f = 1.0MHz	-	6	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time	V _{DD} = 100V	-	9	-	ns
t _r	Turn-on Rise Time	V _{GS} = 15V	-	20	-	
t _{d(OFF)}	Turn-Off Delay Time	I _D = 9A	-	29	-	
t _f	Turn-Off Fall Time	R _G = 3.3Ω	-	27	-	
Q _G	Total Gate-Charge	V _{DD} = 160V	-	22.8	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = 10V	-	6.2	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 18A	-	8.4	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *3	I _{SD} = 18A, V _{GS} = 0V	-	0.84	1.5	V
t _{rr}	Reverse Recovery Time	I _F = 18A, V _R = 100V	-	106	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt = 100A/μs	-	430	-	nC

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
2. The data tested by surface mounted on a minimum recommended FR-4 board
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
4. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 100V, V_{GS} = 15V, L = 50mH$

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

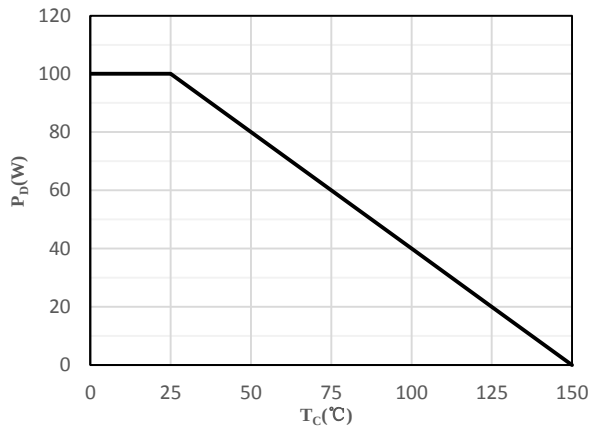


Fig 1 Power Dissipation

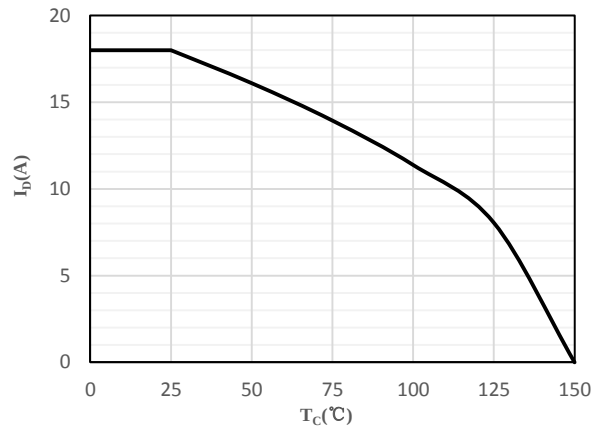


Fig 2 Drain Current

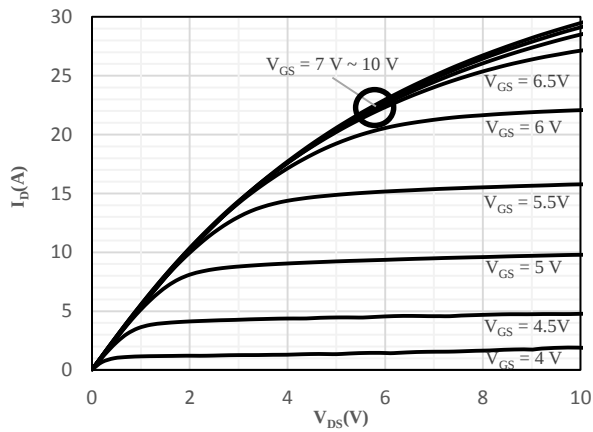


Fig 3 Typical Output Characteristics

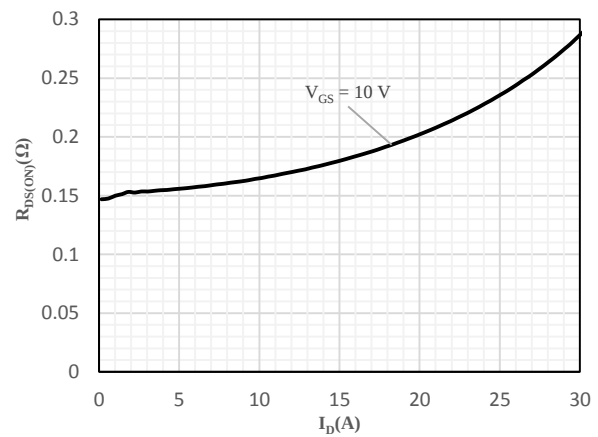


Fig 4 On-Resistance vs. Drain Current
and Gate Voltage

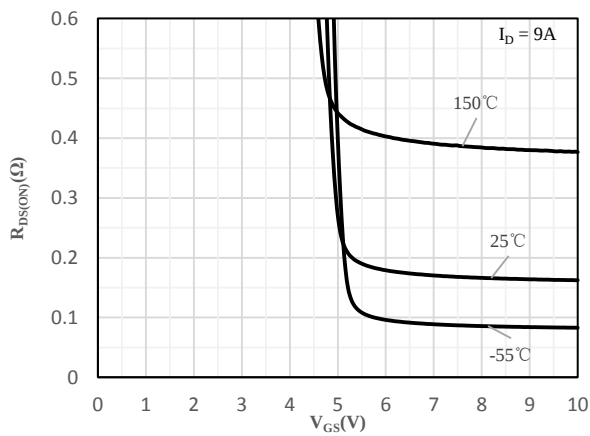


Fig 5 On-Resistance vs. Gate-Source Voltage

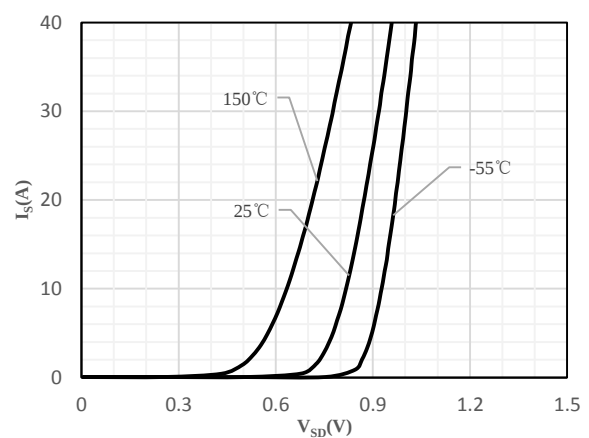


Fig 6 Body-Diode Characteristics

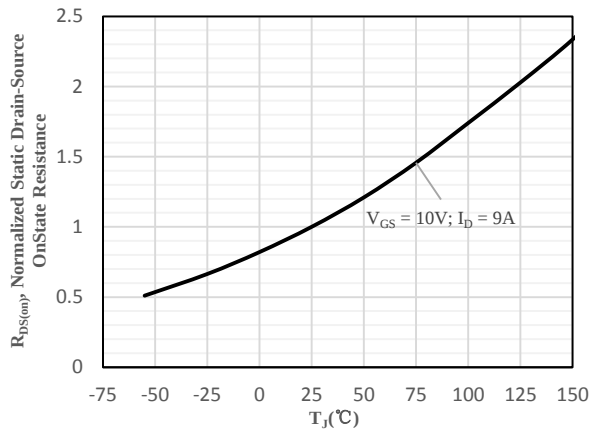


Fig 7 Normalized On-Resistance vs. Junction Temperature

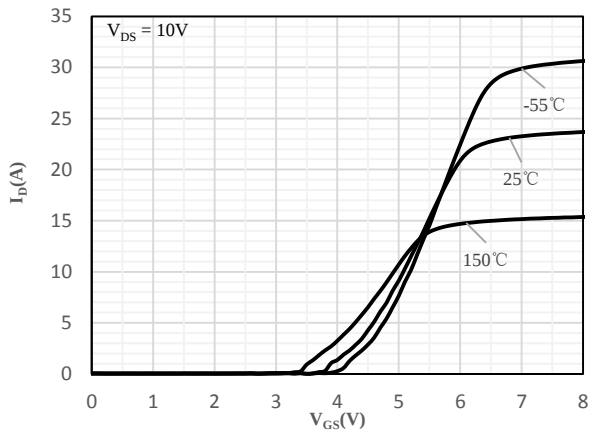


Fig 8 Transfer Characteristics

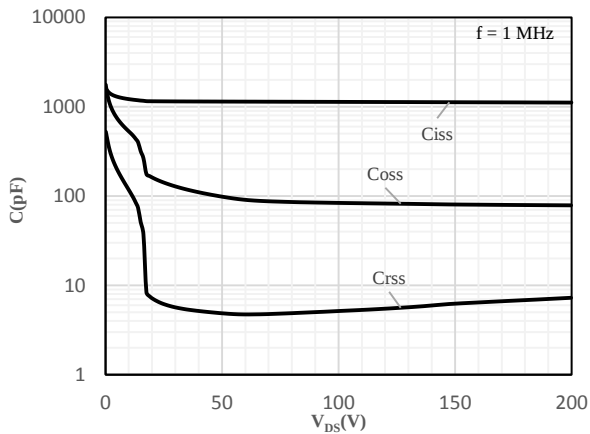


Fig 9 Capacitance Characteristics

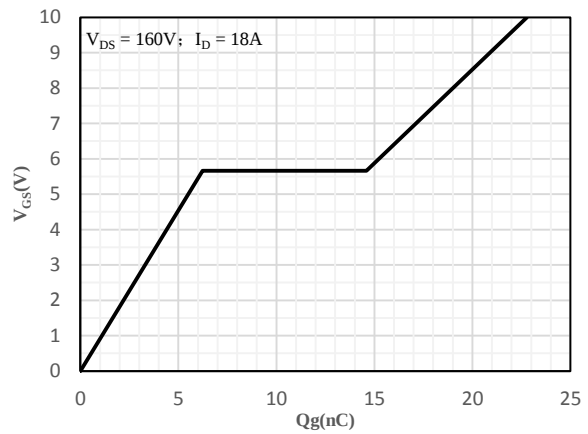


Fig 10 Gate-Charge Characteristics

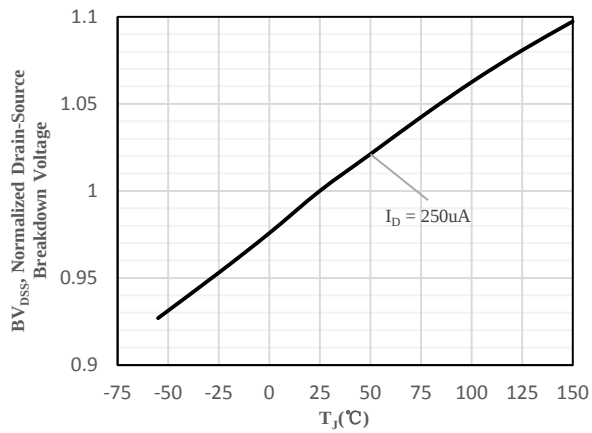


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

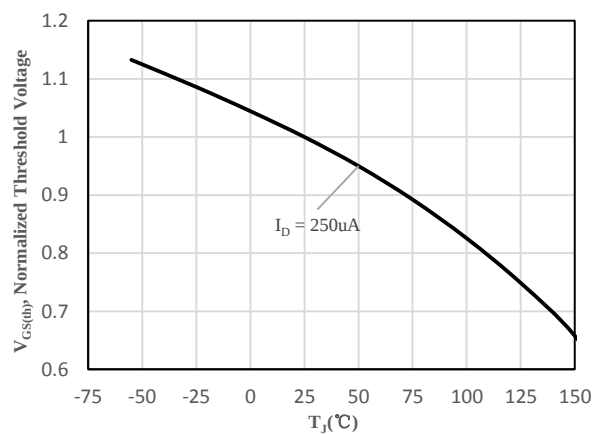


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

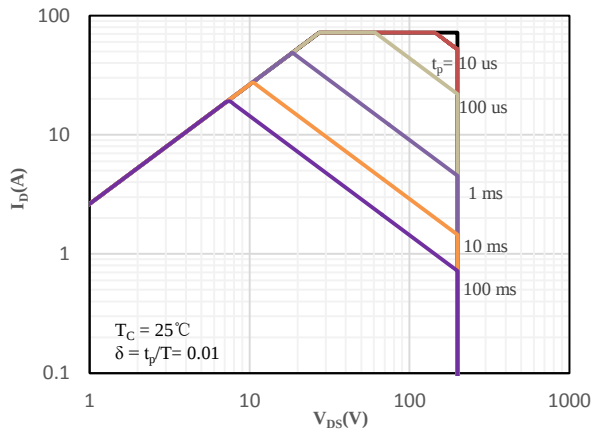


Fig 13 Safe Operation Area

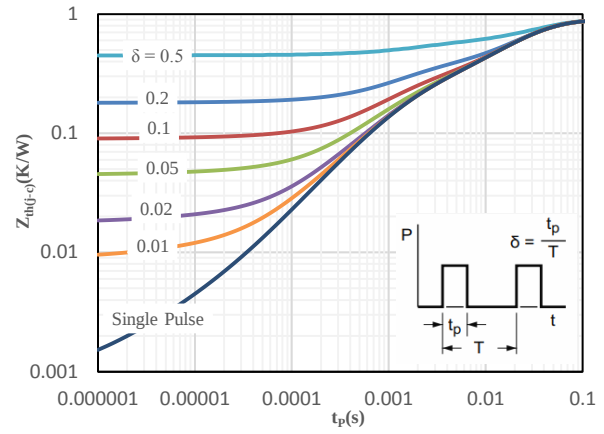
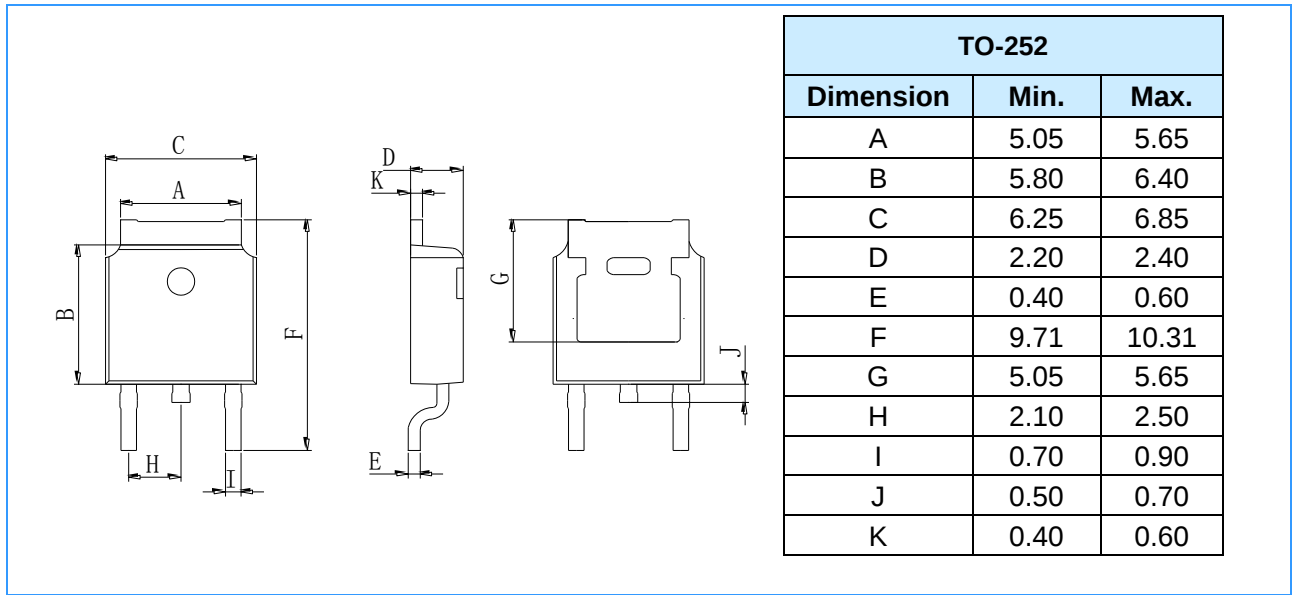
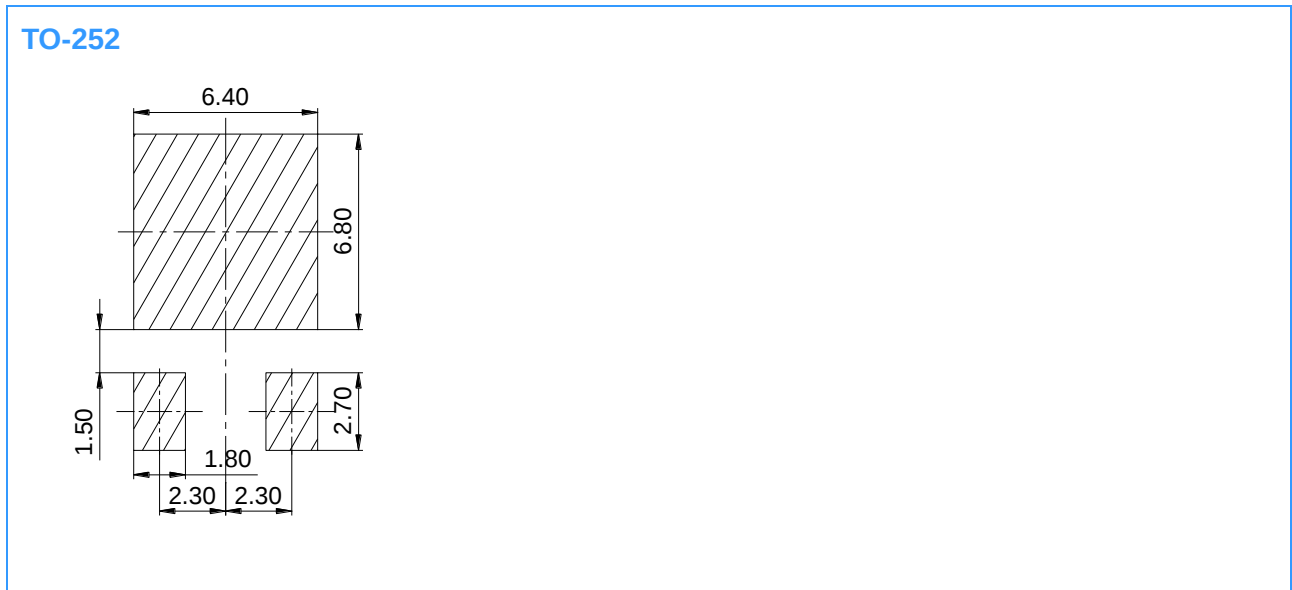


Fig 14 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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